TRANSISTOR ARRAY μ PA2001C, μ PA2002C, μ PA2003C, μ PA2004C

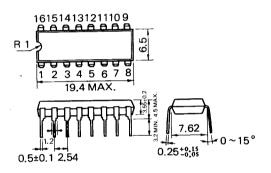
NPN SILICON EPITAXIAL DARLINGTON TRANSISTOR ARRAY

DESCRIPTION

The μ PA2001C, 2002C, 2003C and 2004C are monolithic arrays of seven darlington transistors. These devices are especially suited for driving relays, solenoids, LED, lamps, and other devices with up to 0.3 A output current per unit.

PACKAGE DIMENSIONS

in millimeters



FEATURES

- Transient Protected Outputs
- High DC Current Gain
- High Output Drive Current
- High Output Voltage
- Package is 16 pin Parting grie Copy

Handle With Care

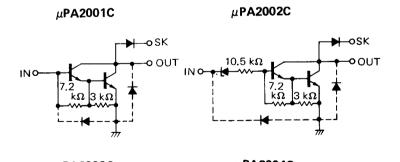
65 (15)

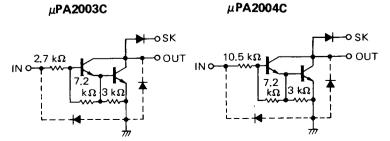
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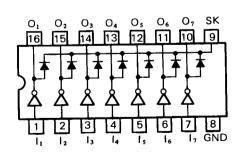
NEC

EQUIVALENT CIRCUIT (1 Unit)





CONNECTION DIAGRAM (Top View)



: Input (Base)

O : Output (Collector)

GND : (Common Emitter)

SK : Surge Killer

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents (Ta = 25 °C)

Output Voltage	٧o	60	V
Input Voltage (except µPA2001C)	VI	-0.5 to +30	V
Input Current (only μ PA2001C)	Ιţ	25	mA/unit
Output Current	10	500	mA/unit
Output Current	10*	2.3	A/package
Reverse Voltage (Clamp Diode)	VR	60	V
Forward Current (Clamp Diode)	ΙĖ	500	mA/unit
Maximum Power Dissipation			
Total Power Dissipation	Pd	900	mW/package
Total Power Dissipation	Pd*	2.5	W/package
Maximum Temperature			
Operating Temperature	Topt	-30 to + 75	°C
Storage Temperature	Tstg	-55 to +150	°C
* 500 450			

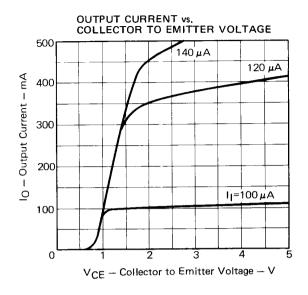
^{*} PW \leq 20 ms, duty cycle \leq 10 %

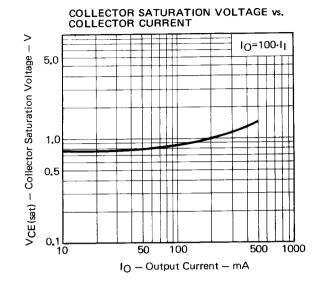
ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

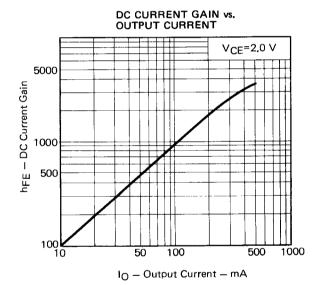
CHARAC	TERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Output Leakage Current		ΙL			10	μΑ	V _{CE} =50 V
					100	μΑ	V _{CE} =50 V, Ta=70 °C
DC Current Gain		hFE	1000	2800			V _{CE} =2.0 V, I _O =350 mA
Collector Saturation Voltage		VCE(sat)		0.9	1,1	V	I _O =100 mA, I _I =250 μA
				1.0	1.3	V	I _O =200 mA, I _I =350 μA
				1.2	1.6	V	I _O =350 mA, I _I =500 μA
Input Voltage	μPA2002C	Vı			11	V	V _{CE} =2.0 V,I _O =100 mA
					12	V	V _{CE} =2.0 V, I _O =200 mA
					13.5	V	V _{CE} =2.0 V, I _O =350 mA
	μPA2003C				2.0	V	V _{CE} =2.0 V, I _O =100 mA
					2.4	V	V _{CE} =2.0 V, I _O =200 mA
					3.4	V	V _{CE} =2.0 V, I _O =350 mA
	μPA2004C				5.0	V	V _{CE} =2.0 V, I _O =100 mA
					6.0	V	V _{CE} =2.0 V, I _O =200 mA
					8.0	V	V _{CE} =2.0 V, I _O =350 mA
Input Current	μPA2002C	ΙΙ			1.3	mA	V _I =17 V
	μPA2003C				1.35	mA	V _I =3.85 V
	μPA2004C				1.0	mA	V _I =5.0 V
Reverse Current (Clamp Diode)		I _R			50	μΑ	V _R =50 V
Forward Voltage (Clamp Diode)		VF			2.0	V	IF=350 mA
Terminal Capacitance		Ct		15		pF	V _I =0, f=1.0 MHz

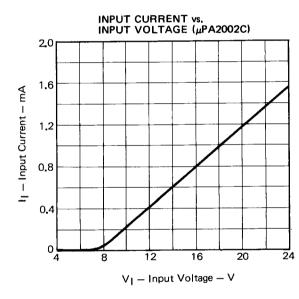
Note: Input Voltage and Current of the $\mu PA2001C$ depend on external resistor.

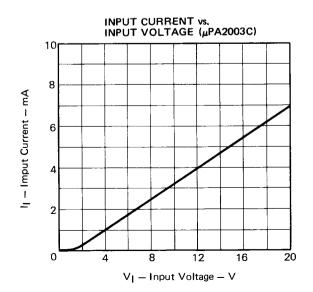
TYPICAL CHARACTERISTICS (Ta = 25 °C)

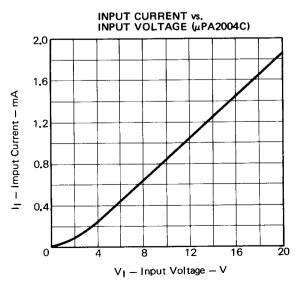


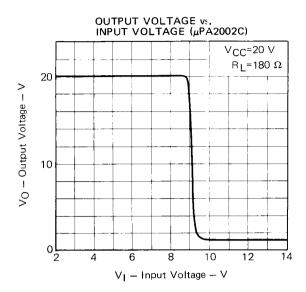


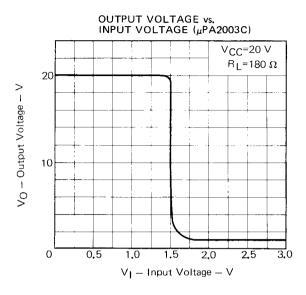




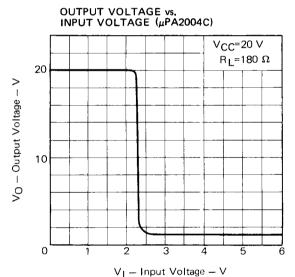


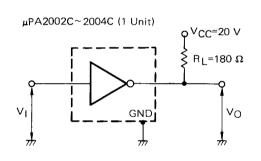






VO-VI TEST CIRCUIT





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Jantx2N6352 Jantx2N6350 BULN2803LVS ULN2001N 2SB1383 2SB1560 2SB852KT146B TIP112TU TIP122TU BCV27 MMBTA13
TP MMBTA14-TP MMSTA28T146 BSP50H6327XTSA1 KSH122TF NTE2557 NJVNJD35N04T4G TIP115 MPSA29-D26Z MJD127T4

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